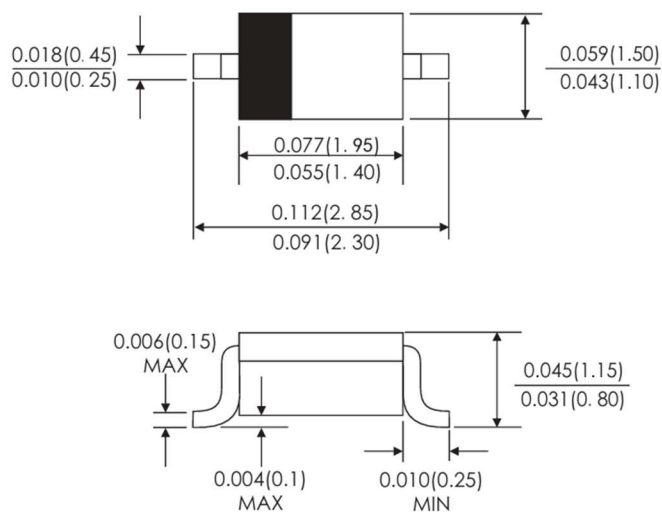


## SWITCHING DIODE

### Features

- For surface mounted applications
- Silicon epitaxial planar diode
- 200mW power dissipation
- Fast switching diode

### SOD-323



Dimensions in inches and (millimeters)

### Order Information

Part Number	Package	Marking	Quantity
1N4448WS	SOD-323	T5	3000

### Absolute Maximum Ratings (T=25°C, unless otherwise specified)

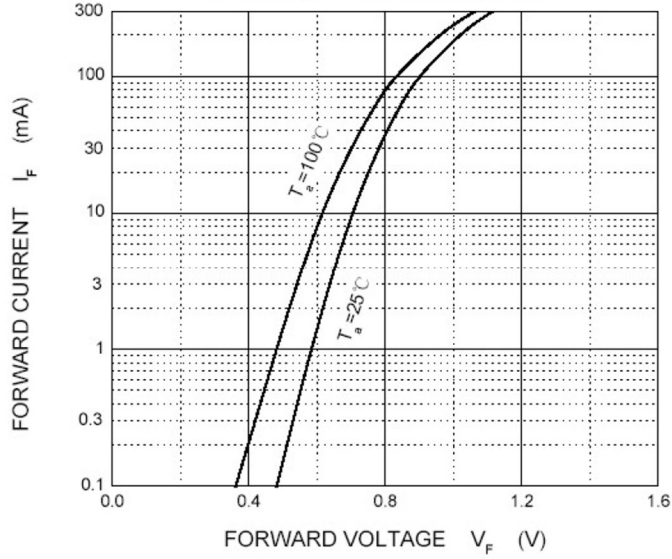
Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Reverse Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	$I_{FM}$	500	mA
Average Rectified Output Current	$I_O$	250	mA
Non-Repetitive Peak Forward Surge Current @ t=1μs	$I_{FSM}$	2	A
Power Dissipation	$P_D$	200	mW
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 ~ +150	°C
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W

**Electrical Characteristics (T=25°C, unless otherwise specified)**

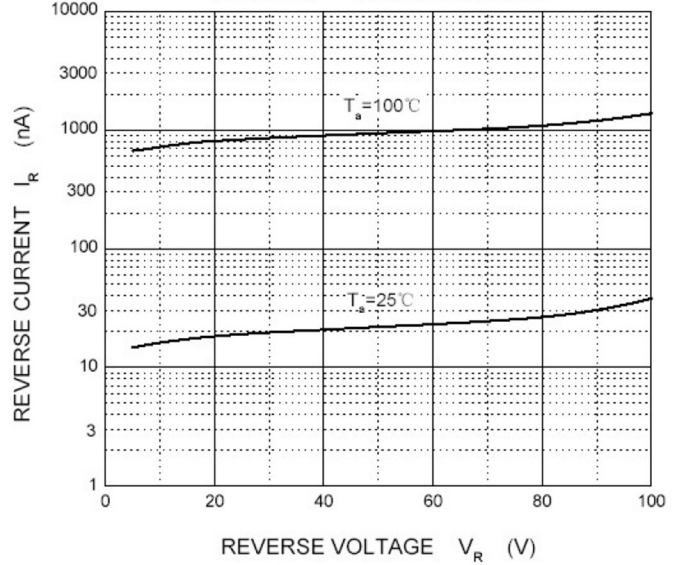
Parameter	Symbol	Test Condition	Min	Max	Unit
Reverse Current	$I_R$	$V_R = 20V$		0.025	$\mu A$
		$V_R = 75V$		2.5	
Forward Voltage	$V_F$	$I_F = 5mA$	0.62	0.72	V
		$I_F = 10mA$		0.855	
		$I_F = 100mA$		1	
		$I_F = 150mA$		1.25	
Capacitance between terminals	$C_T$	$V_R=0, f=1MHZ$		4	pF
Reverse Recovery Time	$T_{rr}$	$I_F=10mA, I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	ns
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=1\mu A$	75		V

**RATINGS AND CHARACTERISTIC CURVES**

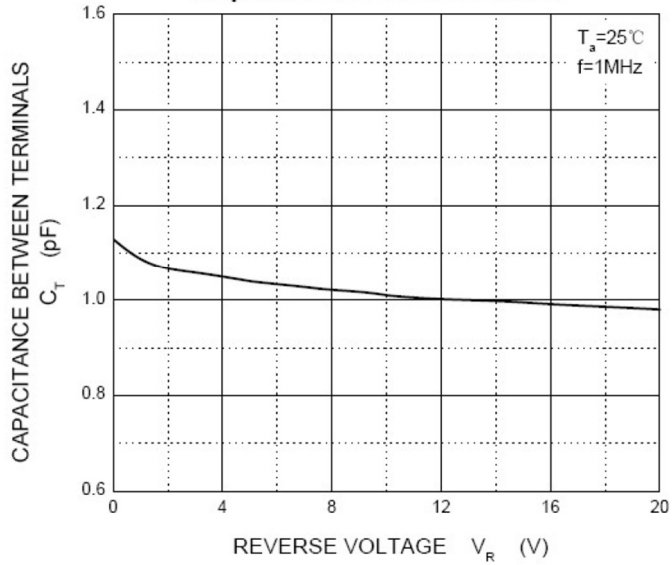
**Forward Characteristics**



**Reverse Characteristics**



**Capacitance Characteristics**



**Power Derating Curve**

